

**Product data sheet** 

### 1. General description

PNP low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

NPN complement: PBSS4330PA.

### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Exposed heat sink for excellent thermal and electrical conductivity
- · Leadless small SMD plastic package with medium power capability

### 3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

### 4. Quick reference data

| Table 1. Quick reference data |   |  |  |     |     |     |      |
|-------------------------------|---|--|--|-----|-----|-----|------|
| Symbol                        | Parameter                               | Conditions   |  | Min | Тур | Max | Unit |
| V <sub>CEO</sub>              | collector-emitter voltage               | open base  |  | -   | -   | -30 | V    |
| I <sub>C</sub>                | collector current                       |  |  | -   | -   | -3  | А    |
| I <sub>CM</sub>               | peak collector current                  | single pulse; t <sub>p</sub> ≤ 1 ms  |  | -   | -   | -5  | А    |
| R <sub>CEsat</sub>            | collector-emitter saturation resistance | I <sub>C</sub> = -3 A; I <sub>B</sub> = -300 mA; pulsed;<br>t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02 ; T <sub>amb</sub> = 25 °C |  | -   | 75  | 107 | mΩ   |

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30 V, 3 A PNP low VCEsat (BISS) transistor

# 5. Pinning information

| Table 2. | Pinning | information |  |                |
|----------|---------|-------------|--|----------------|
| Pin      | Symbol  | Description | Simplified outline                       | Graphic symbol |
| 1        | В       | base        | 3  | 3              |
| 2        | E       | emitter     |  | 1              |
| 3        | С       | collector   |  | 2              |
|          |         |             |  | sym013         |
|          |         |             | Transparent top view DFN2020-3 (SOT1061) |                |

# 6. Ordering information

| Table 3.         Ordering information |           |   |         |  |  |
|---------------------------------------|-----------|---|---------|--|--|
| Type number Package                   |           |   |         |  |  |
|                                       | Name      | Description   | Version |  |  |
| PBSS5330PA                            | DFN2020-3 | DFN2020-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 2 x 2 x 0.65 mm | SOT1061 |  |  |

### 7. Marking

| Table 4. Marking codes |              |
|------------------------|--------------|
| Type number            | Marking code |
| PBSS5330PA             | AJ           |

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### 8. Limiting values

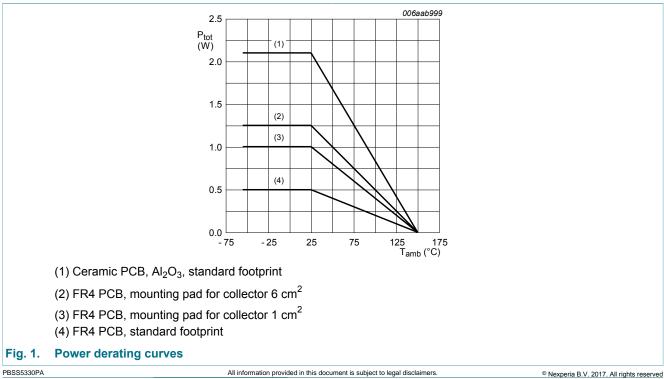
#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                 | Conditions                          |     | Min | Max  | Unit |
|------------------|---------------------------|-------------------------------------|-----|-----|------|------|
| V <sub>CBO</sub> | collector-base voltage    | open emitter                        |     | -   | -30  | V    |
| V <sub>CEO</sub> | collector-emitter voltage | open base                           |     | -   | -30  | V    |
| V <sub>EBO</sub> | emitter-base voltage      | open collector                      |     | -   | -6   | V    |
| I <sub>C</sub>   | collector current         |                                     |     | -   | -3   | А    |
| I <sub>CM</sub>  | peak collector current    | single pulse; t <sub>p</sub> ≤ 1 ms |     | -   | -5   | А    |
| I <sub>B</sub>   | base current              |                                     |     | -   | -500 | mA   |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | [1] | -   | 500  | mW   |
|                  |                           |                                     | [2] | -   | 1    | W    |
|                  |                           |                                     | [3] | -   | 1.25 | W    |
|                  |                           |                                     | [4] | -   | 2.1  | W    |
| Tj               | junction temperature      |                                     |     | -   | 150  | °C   |
| T <sub>amb</sub> | ambient temperature       |                                     |     | -55 | 150  | °C   |
| T <sub>stg</sub> | storage temperature       |                                     |     | -65 | 150  | °C   |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

- <sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- <sup>[3]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB,  $Al_2O_3$ , standard footprint.

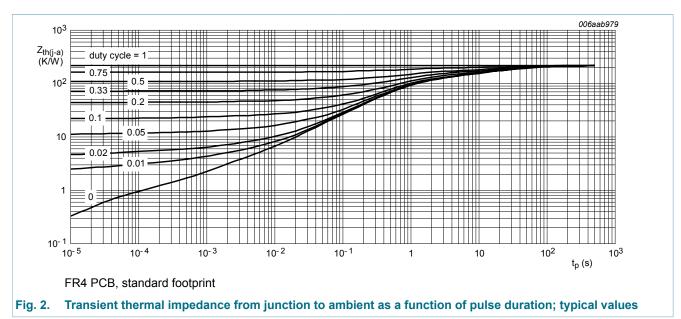


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### 9. Thermal characteristics

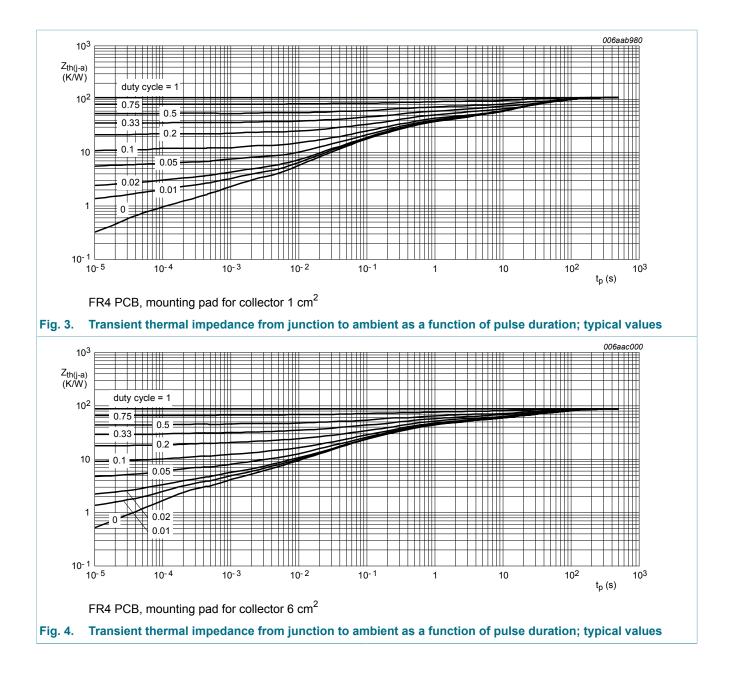
| Table 6. Thermal characteristics                                       |             |            |     |     |     |     |      |
|--|-------------|------------|-----|-----|-----|-----|------|
| Symbol   | Parameter   | Conditions |     | Min | Тур | Max | Unit |
| R <sub>th(j-a)</sub> thermal resistance<br>from junction to<br>ambient | in free air | [1]        | -   | -   | 250 | K/W |      |
|  |             | [2]        | -   | -   | 125 | K/W |      |
|  |             | [3]        | -   | -   | 100 | K/W |      |
|  |             |            | [4] | -   | -   | 60  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB,  $Al_2O_3$ , standard footprint.





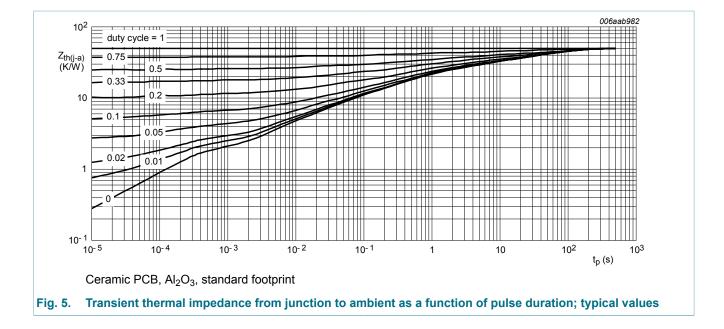
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## PBSS5330PA

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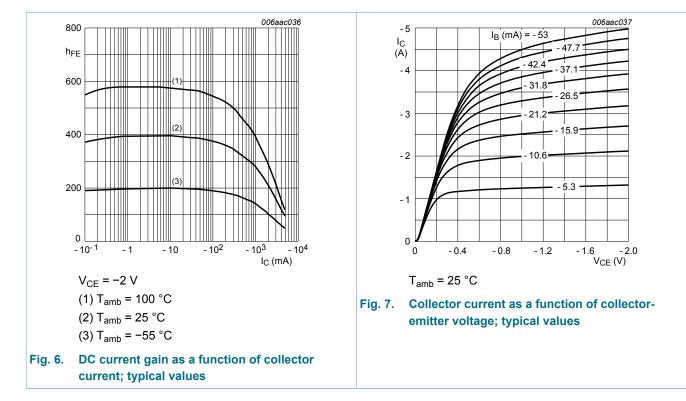
### **10. Characteristics**

| Symbol   | Parameter   | Conditions  | Min | Тур   | Max  | Unit |
|--|---|---|-----|-------|------|------|
| I <sub>CBO</sub>   | collector-base cut-off  | $V_{CB}$ = -30 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C  | -   | -     | -100 | nA   |
|  | current   | $V_{CB}$ = -30 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C   | -   | -     | -50  | μA   |
| I <sub>CES</sub>   | collector-emitter cut-off current   | $V_{CE}$ = -24 V; $V_{BE}$ = 0 V; $T_{amb}$ = 25 °C   | -   | -     | -100 | nA   |
| I <sub>EBO</sub>   | emitter-base cut-off current  | $V_{EB}$ = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C   | -   | -     | -100 | nA   |
| h <sub>FE</sub>  | DC current gain   | $\begin{split} &V_{CE} \texttt{=-2 V; I}_{C} \texttt{=-0.5 A; pulsed;} \\ &t_{p} \texttt{\leq 300 } \mu\texttt{s; } \delta \texttt{\leq 0.02 }; T_{amb} \texttt{= 25 }^{\circ}\texttt{C} \end{split}$ | 200 | 320   | -    |      |
|  |   | $\begin{split} V_{CE} &= -2 \text{ V}; \text{ I}_{C} = -1 \text{ A}; \text{ pulsed}; \\ t_{p} &\leq 300  \mu\text{s};  \overline{\delta} &\leq 0.02 ;  T_{amb} = 25 ^{\circ}\text{C} \end{split}$     | 175 | 280   | 450  |      |
|  | $V_{CE}$ = -2 V; I <sub>C</sub> = -2 A; pulsed;<br>t <sub>p</sub> ≤ 300 µs; $\overline{\delta}$ ≤ 0.02 ; T <sub>amb</sub> = 25 °C | 140   | 210 | -     |      |      |
|  |   | $V_{CE} = -2 \text{ V; } I_C = -3 \text{ A; pulsed;}$<br>$t_p \le 300  \mu\text{s; } \overline{\delta} \le 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C}$   | 100 | 160   | -    |      |
| V <sub>CEsat</sub> collector-emitter<br>saturation voltage |   | $\begin{split} I_C &= -0.5 \text{ A};  I_B = -50 \text{ mA}; \text{ pulsed}; \\ t_p &\leq 300  \mu\text{s};  \delta \leq 0.02  ;  T_{\text{amb}} = 25 ^\circ\text{C} \end{split}$                     | -   | -45   | -70  | mV   |
|  |   | $\begin{split} I_C &= -1 \text{ A};  I_B = -50 \text{ mA}; \text{ pulsed}; \\ t_p &\leq 300  \mu\text{s};  \delta \leq 0.02  ;  T_{amb} = 25 ^\circ\text{C} \end{split}$                              | -   | -90   | -130 | mV   |
|  |   | $\begin{split} I_{C} &= -2 \text{ A};  I_{B} = -100 \text{ mA}; \text{ pulsed}; \\ t_{p} &\leq 300  \mu\text{s};  \overline{\delta} &\leq 0.02  ;  T_{amb} = 25 ^{\circ}\text{C} \end{split}$         | -   | -170  | -240 | mV   |
|  |   | $I_{C}$ = -3 A; $I_{B}$ = -300 mA; pulsed;  | -   | -230  | -320 | mV   |
| R <sub>CEsat</sub>   | collector-emitter saturation resistance   | $t_p$ ≤ 300 μs; δ ≤ 0.02 ; T <sub>amb</sub> = 25 °C   | -   | 75    | 107  | mΩ   |
| V <sub>BEsat</sub>   | base-emitter saturation voltage   | $\begin{split} I_{C} &= -2 \text{ A};  I_{B} = -100 \text{ mA}; \text{ pulsed}; \\ t_{p} &\leq 300  \mu\text{s};  \delta \leq 0.02  ;  T_{amb} = 25 ^{\circ}\text{C} \end{split}$                     | -   | -0.89 | -1.1 | V    |
|  |   | $\begin{split} I_C &= -3 \text{ A};  I_B = -300 \text{ mA}; \text{ pulsed}; \\ t_p &\leq 300  \mu\text{s};  \delta \leq 0.02  ;  T_{\text{amb}} = 25 ^\circ\text{C} \end{split}$                      | -   | -0.97 | -1.2 | V    |
| V <sub>BEon</sub>  | base-emitter turn-on voltage  | $V_{CE}$ = -2 V; I <sub>C</sub> = -1 A; pulsed;<br>t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02 ; T <sub>amb</sub> = 25 °C  | -   | -0.75 | -1   | V    |
| t <sub>d</sub>   | delay time  | V <sub>CC</sub> = -9 V; I <sub>C</sub> = -2 A; I <sub>Bon</sub> = -0.1 A;   | -   | 11    | -    | ns   |
| t <sub>r</sub>   | rise time   | $I_{Boff}$ = 0.1 A; $T_{amb}$ = 25 °C   | -   | 59    | -    | ns   |
| t <sub>on</sub>  | turn-on time  |   | -   | 70    | -    | ns   |
| t <sub>s</sub>   | storage time  |   | -   | 165   | -    | ns   |
| t <sub>f</sub>   | fall time   |   | -   | 35    | -    | ns   |
| t <sub>off</sub>   | turn-off time   |   | -   | 200   | -    | ns   |

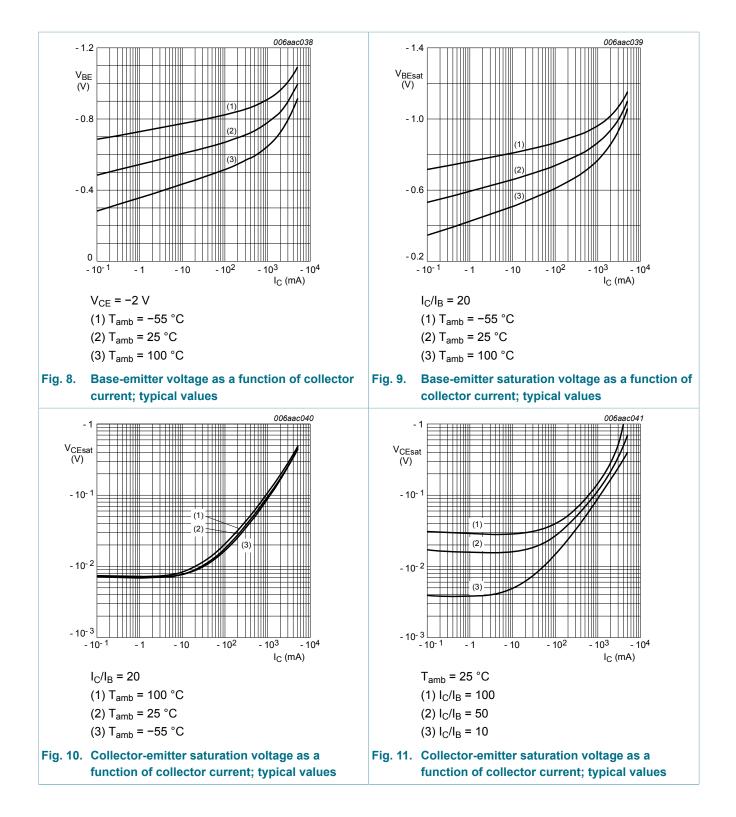
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| Symbol         | Parameter             | Conditions  | Min | Тур | Max | Unit |
|----------------|-----------------------|---|-----|-----|-----|------|
| f <sub>T</sub> | transition frequency  | $V_{CE}$ = -5 V; I <sub>C</sub> = -100 mA; f = 100 MHz;<br>T <sub>amb</sub> = 25 °C                         | 100 | 165 | -   | MHz  |
| C <sub>c</sub> | collector capacitance | V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A;<br>f = 1 MHz; T <sub>amb</sub> = 25 °C | -   | 38  | 45  | pF   |



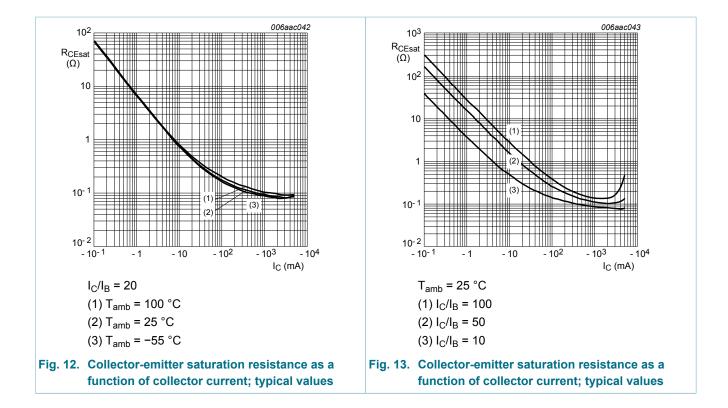
#### 30 V, 3 A PNP low VCEsat (BISS) transistor



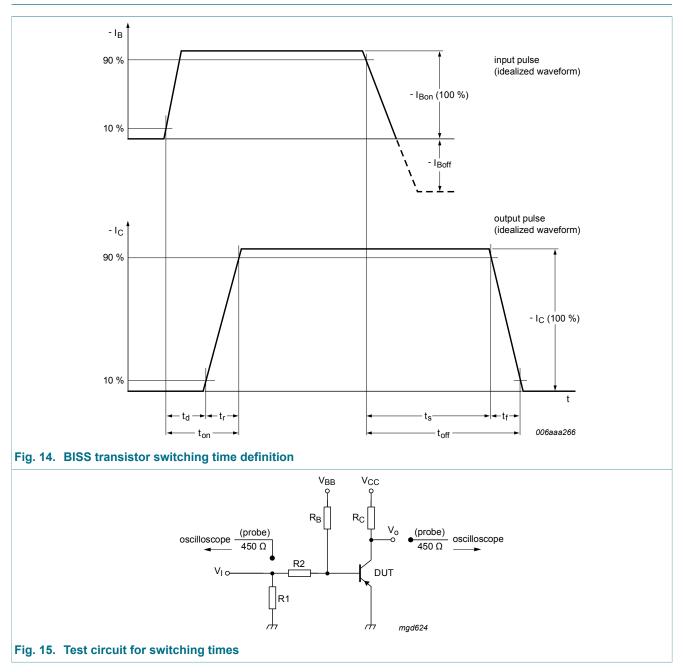
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# PBSS5330PA

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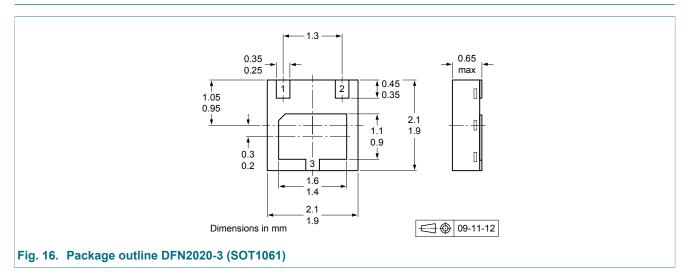
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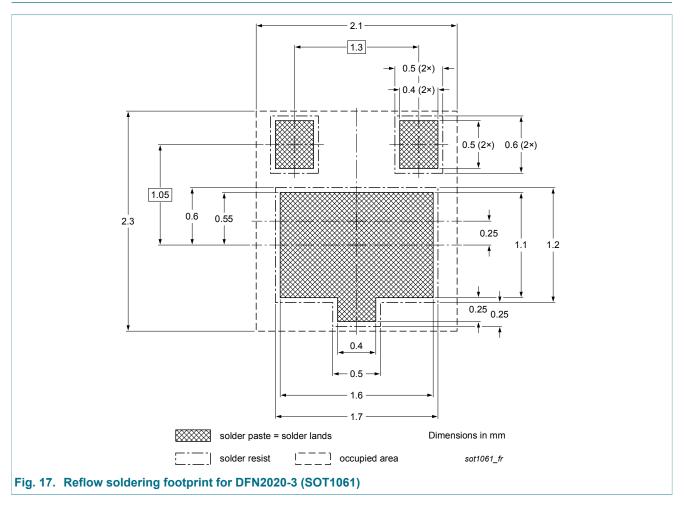
### **11. Test information**

#### 30 V, 3 A PNP low VCEsat (BISS) transistor

### 12. Package outline



### 13. Soldering



#### 30 V, 3 A PNP low VCEsat (BISS) transistor

# 14. Revision history

| Table 8. Revision hi | story                          |                                       |                          |                |
|----------------------|--------------------------------|---------------------------------------|--------------------------|----------------|
| Data sheet ID        | Release date                   | Data sheet status                     | Change notice            | Supersedes     |
| PBSS5330PA v.2       | 20150407                       | Product data sheet                    | -                        | PBSS5330PA v.1 |
| Modifications:       | Condition V <sub>CE</sub> chan | ged for parameter I <sub>CES</sub> in | Table 7, Characteristics |                |
| PBSS5330PA v.1       | 20100419                       | Product data sheet                    | -                        | -              |

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### 15. Legal information

#### 15.1 Data sheet status

| Document<br>status [1][2]            | Product<br>status [ <u>3]</u> | Definition  |
|--------------------------------------|-------------------------------|---|
| Objective<br>[short] data<br>sheet   | Development                   | This document contains data from<br>the objective specification for product<br>development. |
| Preliminary<br>[short] data<br>sheet | Qualification                 | This document contains data from the preliminary specification.                             |
| Product<br>[short] data<br>sheet     | Production                    | This document contains the product specification.   |

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